

Title (en)  
SOLAR CELLS WITH A BARRIER LAYER BASED ON POLYSILAZANE

Title (de)  
SOLARZELLEN MIT EINER BARRIERESCHICHT AUF BASIS VON POLYSILAZAN

Title (fr)  
CELLULES SOLAIRES POURVUES D'UNE COUCHE BARRIÈRE À BASE DE POLYSILAZANE

Publication  
**EP 2409336 A1 20120125 (DE)**

Application  
**EP 10709428 A 20100316**

Priority  
• EP 2010001638 W 20100316  
• DE 102009013903 A 20090319

Abstract (en)  
[origin: WO2010105798A1] The invention relates to a thin-film solar cell (10) comprising a substrate (1) of metal or glass, a dielectric barrier layer (2) based on polysilazane and a photovoltaic layer structure (4) of the copper-indium sulphide (CIS) type or the copper-indium-gallium selenide (CIGSe) type.

IPC 8 full level  
**H01L 31/032** (2006.01)

CPC (source: EP US)  
**C08G 77/62** (2013.01 - EP US); **C09D 183/16** (2013.01 - EP US); **H01L 31/03923** (2013.01 - EP US); **H01L 31/0749** (2013.01 - EP US); **Y02E 10/541** (2013.01 - EP US); **Y02P 70/50** (2015.11 - EP US)

Citation (search report)  
See references of WO 2010105798A1

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Designated contracting state (EPC)  
AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL PT RO SE SI SK SM TR

DOCDB simple family (publication)  
**DE 102009013903 A1 20100923**; CN 102414828 A 20120411; CN 102414828 B 20150527; EP 2409336 A1 20120125; JP 2012521081 A 20120910; JP 5653994 B2 20150114; US 2012006403 A1 20120112; US 9234119 B2 20160112; WO 2010105798 A1 20100923

DOCDB simple family (application)  
**DE 102009013903 A 20090319**; CN 201080018736 A 20100316; EP 10709428 A 20100316; EP 2010001638 W 20100316; JP 2012500138 A 20100316; US 201013257037 A 20100316